IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-59. (Canceled)

60. (Currently Amended) A method of manufacturing a display device comprising the steps of:

forming a semiconductor film ~~plurality of thin film transistors~~ over a substrate;

forming a first insulating film over the semiconductor film;

forming a gate electrode over the first insulating film;

forming a second insulating film over the gate electrode wherein the second insulating film has a contact hole;

forming one of a source wiring and a drain wiring over the second insulating film wherein one of the source wiring and the drain wiring is electrically connected to the semiconductor film through the contact hole of the second insulating film;

forming a third insulating film over one of the source wiring and the drain wiring;

forming [[an]] a fourth insulating film comprising a resin over the third insulating film ~~plurality of thin film transistors~~;

forming a fifth insulating ~~passivation~~ film over the fourth insulating film; and

forming an electroluminescence element over the fourth insulating ~~passivation~~ film, said electroluminescence element comprising a first electrode formed in contact with the fifth insulating ~~passivation~~ film, ~~a light emitting~~ an electroluminescence layer formed over the first

electrode by an ink jet method and a second electrode formed over the electroluminescence ~~light emitting~~ layer,

~~wherein said first electrode is electrically connected to one of said thin film transistors through a contact hole through said passivation film and said insulating film,~~

wherein the electroluminescence ~~light emitting~~ layer is in contact with an upper surface of the fifth insulating ~~passivation~~ film.

61. (Canceled)

62. (Currently Amended) A method of manufacturing a display device according to claim 60, wherein each of the third and fifth insulating ~~passivation~~ films comprises an insulating film that comprises at least an element selected from a group consisting of B (boron), C (carbon) and N (nitrogen) and an element selected from a group consisting of Al (aluminum), Si (silicon) and P (phosphorus), or an insulating film that comprises Si, Al, N, O and M where M is a rare earth element preferably one selected from a group consisting of Ce (cerium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), La (lanthanum), Gd (gadolinium), Dy (dysprosium) and Nd (neodymium).

63. (Currently Amended) A method of manufacturing a display device according to claim 60, wherein said each of the third and fifth insulating ~~passivation~~ films comprises a material selected from the group consisting of silicon nitride and silicon oxynitride.

64. (Currently Amended) A method of manufacturing a display device according to claim 60, wherein said electroluminescence ~~light-emitting~~ layer comprises an organic light emitting layer.

65. (Currently Amended) A method of manufacturing a display device comprising the steps of:

forming a semiconductor film ~~plurality of thin film transistors~~ over a substrate;

forming a first insulating film over the semiconductor film;

forming a gate electrode over the first insulating film;

forming a second insulating film over the gate electrode wherein the second insulating film has a contact hole;

forming one of a source wiring and a drain wiring over the second insulating film wherein one of the source wiring and the drain wiring is electrically connected to the semiconductor film through the contact hole of the second insulating film;

forming a third insulating film over one of the source wiring and the drain wiring;

forming [[an]] a fourth insulating film comprising a resin over the third insulating film ~~plurality of thin film transistors~~;

forming a fifth insulating ~~first passivation~~ film over the fourth insulating film; and

forming an electroluminescence element over the fourth insulating ~~first passivation~~ film, said electroluminescence element comprising a first electrode formed in contact with the fifth insulating ~~first passivation~~ film, a second electrode and ~~a light emitting~~ an electroluminescence layer interposed therebetween~~; and~~

~~forming a second passivation film over the electroluminescence element~~,

wherein the electroluminescence layer is in contact with an upper surface of the fifth insulating film, and

wherein the electroluminescence ~~light emitting~~ layer, and the second electrode ~~and the second passivation film~~ are formed in succession without exposure to an atmosphere.

66. (Canceled)

67. (Currently Amended) A method of manufacturing a display device according to claim 65, wherein each of ~~the first passivation film and~~ the third and fifth insulating ~~second passivation~~ films comprises at least an element selected from a group consisting of B (boron), C (carbon) and N (nitrogen) and an element selected from a group consisting of Al (aluminum), Si (silicon) and P (phosphorus).

68. (Currently Amended) A method of manufacturing a display device according to claim 65, wherein each of ~~the first passivation film and~~ the third and fifth insulating ~~second passivation~~ films comprises Si, Al, N, O and M where M is a rare earth element preferably one selected from a group consisting of Ce (cerium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), La (lanthanum), Gd (gadolinium), Dy (dysprosium) and Nd (neodymium).

69. (Currently Amended) A method of manufacturing a display device according to claim 65, further comprising a step of forming an insulating film that comprises at least an element selected from a group consisting of B (boron), C (carbon) and N (nitrogen) and an element selected from a group consisting of Al (aluminum), Si (silicon) and P (phosphorus), between the substrate and the semiconductor film ~~plurality of thin film transistors~~.

70. (Currently Amended) A method of manufacturing a display device according to claim 65, further comprising a step of forming an insulating film that comprises Si, Al, N, O and M where M is a rare earth element preferably one selected from a group consisting of Ce (cerium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), La (lanthanum), Gd (gadolinium), Dy (dysprosium) and Nd (neodymium), between the substrate and the semiconductor film ~~plurality of thin film transistors~~.

71. (Currently Amended) A method of manufacturing a display device comprising the steps of:

forming a semiconductor film ~~plurality of thin film transistors~~ over a substrate;

forming a first insulating film over the semiconductor film;

forming a gate electrode over the first insulating film;

forming a second insulating film over the gate electrode wherein the second insulating film has a contact hole;

forming one of a source wiring and a drain wiring over the second insulating film wherein one of the source wiring and the drain wiring is electrically connected to the semiconductor film through the contact hole of the second insulating film;

forming a third insulating film over one of the source wiring and the drain wiring;

forming a leveling film comprising a resin over the third insulating film ~~plurality of thin film transistors~~;

forming [[an]] a fourth insulating ~~passivation~~ film over the leveling film; and

forming an electroluminescence element over the leveling ~~passivation~~ film, said electroluminescence element comprising a first electrode formed in contact with the fourth

insulating ~~passivation~~ film, a second electrode and ~~a light emitting~~ an electroluminescence layer interposed therebetween,

wherein the electroluminescence ~~light emitting~~ layer is formed by an ink jet method so as to be in contact with an upper surface of the fourth insulating ~~passivation~~ film.

72. (Canceled)

73. (Currently Amended) A method of manufacturing a display device according to claim 71, wherein each of said third and fourth ~~passivation~~ films comprises a material selected from the group consisting of silicon nitride and silicon oxynitride.

74. (Currently Amended) A method of manufacturing a display device according to claim 71, wherein said electroluminescence ~~light emitting~~ layer comprises an organic light emitting layer.

75. (Currently Amended) A method of manufacturing a display device comprising the steps of:

forming a semiconductor film ~~thin film transistor~~ over a substrate;

forming a first insulating film over the semiconductor film;

forming a gate electrode over the first insulating film;

forming a second insulating film over the gate electrode wherein the second insulating film has a contact hole;

forming one of a source wiring and a drain wiring over the second insulating film wherein one of the source wiring and the drain wiring is electrically connected to the semiconductor film through the contact hole of the second insulating film;

forming a third ~~first~~ insulating film comprising silicon and nitrogen over one of the source wiring and the drain wiring ~~the thin film transistor~~;

forming a leveling film comprising a resin over the third ~~first~~ insulating film;

forming a fourth ~~second~~ insulating film ~~comprising silicon nitride~~ over the leveling film; and

forming an electroluminescence ~~light emitting~~ element over the leveling ~~second~~ insulating film, said electroluminescence ~~light emitting~~ element comprising a first electrode formed in contact with the fourth ~~second~~ insulating film, a second electrode and ~~a light emitting~~ an electroluminescence layer interposed therebetween~~; and~~

~~forming a third insulating film comprising a material selected from the group consisting of aluminum nitride, silicon carbide, silicon nitride, boron nitride, boron phosphate and aluminum oxide~~,

wherein the electroluminescence layer is in contact with an upper surface of the fourth insulating film, and

wherein the electroluminescence ~~light emitting~~ layer, and the second electrode ~~and the third insulating film~~ are formed in succession without exposure to an atmosphere.

76. (Currently Amended) A display device comprising:

a substrate;

a semiconductor film formed over the substrate;

a first insulating film formed over the semiconductor film;

a gate electrode formed over the first insulating film;

a second insulating film formed over the gate electrode wherein the second insulating film has a contact hole;

one of a source wiring and a drain wiring formed over the second insulating film wherein one of the source wiring and the drain wiring is electrically connected to the semiconductor film through the contact hole of the second insulating film

~~a thin film transistor formed over the substrate, said thin film transistor comprising at least a semiconductor film and a gate electrode adjacent to the semiconductor film with a gate insulating film there between;~~

a third ~~first~~ insulating film formed over one of the source wiring and the drain wiring ~~the semiconductor film and the gate electrode~~;

a leveling film comprising a resin formed over the third ~~first~~ insulating film;

a fourth ~~second~~ insulating film formed over the leveling film; and

an electroluminescence ~~light emitting~~ element formed over the leveling ~~second insulating~~ film, said electroluminescence ~~light emitting~~ element comprising a first electrode formed in contact with the fourth ~~second~~ insulating film, an electroluminescence layer formed over the first electrode and a second electrode formed over the electroluminescence layer~~; and~~

~~a third insulating film formed over the second electrode~~,

wherein the electroluminescence layer is in contact with an upper surface of the fourth insulating film.

77. (Canceled)

78. (Currently Amended) A display device according to claim 76, wherein a storage capacitor is formed by the semiconductor film, the [[gate]] first insulating film and a capacitor electrode.

79. (Currently Amended) A display device according to claim 76, wherein each of the ~~first~~ third and fourth insulating films comprises silicon, nitrogen and oxygen.

80. (Previous Presented) A display device according to claim 76, wherein the second insulating film comprises silicon nitride.

81. (Currently Amended) A display device according to claim 76, wherein the second ~~third~~ insulating film comprises C (carbon) ~~a material selected from the group consisting of aluminum nitride, silicon carbide, silicon nitride, boron nitride, boron phosphate and aluminum oxide~~.

82. (New) A method of manufacturing a display device according to claim 60, wherein the fifth insulating film comprises C (carbon).

83. (New) A method of manufacturing a display device according to claim 65, wherein the fifth insulating film comprises C (carbon).

84. (New) A method of manufacturing a display device according to claim 71, wherein the fourth insulating film comprises C (carbon).

85. (New) A method of manufacturing a display device according to claim 75, wherein the fourth insulating film comprises C (carbon).

86. (New) A method of manufacturing a display device according to claim 60, wherein the fourth insulating film comprises a material selected from the group consisting of polyimide, polyamide, acrylic, and BCB (benzocyclobutane).

87. (New) A method of manufacturing a display device according to claim 65, wherein the fourth insulating film comprises a material selected from the group consisting of polyimide, polyamide, acrylic, and BCB (benzocyclobutane).

88. (New) A method of manufacturing a display device according to claim 71, wherein the leveling film comprises a material selected from the group consisting of polyimide, polyamide, acrylic, and BCB (benzocyclobutane).

89. (New) A method of manufacturing a display device according to claim 75, wherein the leveling film comprises a material selected from the group consisting of polyimide, polyamide, acrylic, and BCB (benzocyclobutane).

90. (New) A display device according to claim 76, wherein the leveling film comprises a material selected from the group consisting of polyimide, polyamide, acrylic, and BCB (benzocyclobutane).